



# FDZ191P

## P-Channel 1.5V PowerTrench® WL-CSP MOSFET

-20V, -1A, 85mΩ

### Features

- Max  $r_{DS(on)}$  = 85mΩ at  $V_{GS} = -4.5V$ ,  $I_D = -1A$
- Max  $r_{DS(on)}$  = 123mΩ at  $V_{GS} = -2.5V$ ,  $I_D = -1A$
- Max  $r_{DS(on)}$  = 200mΩ at  $V_{GS} = -1.5V$ ,  $I_D = -1A$
- Occupies only 1.5 mm<sup>2</sup> of PCB area Less than 50% of the area of 2 x 2 BGA
- Ultra-thin package: less than 0.65 mm height when mounted to PCB
- RoHS Compliant

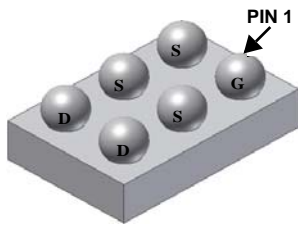


### General Description

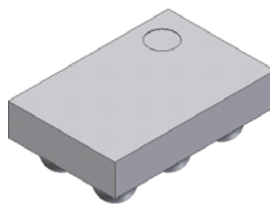
Designed on Fairchild's advanced 1.5V PowerTrench process with state of the art "low pitch" WLCSP packaging process, the FDZ191P minimizes both PCB space and  $r_{DS(on)}$ . This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge, and low  $r_{DS(on)}$ .

### Application

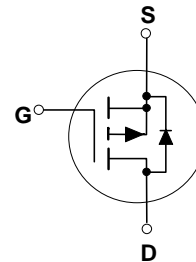
- Battery management
- Load switch
- Battery protection



BOTTOM



TOP



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rated Value	Units
$V_{DS}$	Drain to Source Voltage	-20	V
$V_{GS}$	Gate to Source Voltage	±8	V
$I_D$	Drain Current -Continuous	-3	A
	-Pulsed	-15	
$P_D$	Power Dissipation	1.5	W
	Power Dissipation	0.9	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	83	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	140	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1	FDZ191P	WL-CSP	7"	8mm	5000 units

## Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = -250\mu\text{A}, V_{GS} = 0\text{V}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-12		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu\text{A}$	-0.4	-0.6	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250\mu\text{A}$ , referenced to $25^\circ\text{C}$		2		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Drain to Source On Resistance	$V_{GS} = -4.5\text{V}, I_D = -1\text{A}$		67	85	m $\Omega$
		$V_{GS} = -2.5\text{V}, I_D = -1\text{A}$		85	123	
		$V_{GS} = -1.5\text{V}, I_D = -1\text{A}$		140	200	
		$V_{GS} = -4.5\text{V}, I_D = -1\text{A}, T_J = 125^\circ\text{C}$		87	123	
$I_{D(on)}$	On to State Drain Current	$V_{GS} = -4.5\text{V}, V_{DS} = -5\text{V}$	-10			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -1\text{A}$		7		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		800		pF
$C_{oss}$	Output Capacitance			155		pF
$C_{rss}$	Reverse Transfer Capacitance			90		pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		9		$\Omega$

### Switching Characteristics

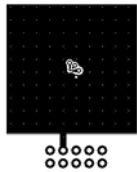
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -10\text{V}, I_D = -1\text{A}$ $V_{GS} = -4.5\text{V}, R_{GEN} = 6\Omega$		11	20	ns
$t_r$	Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			50	80	ns
$t_f$	Fall Time			30	48	ns
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$	$V_{DD} = -10\text{V}$ $I_D = -1\text{A}$	9	13	nC
$Q_{gs}$	Gate to Source Gate Charge			1		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			2		nC

### Drain-Source Diode Characteristics

$I_S$	Maximum continuous Drain-Source Diode Forward Current				-1.1	A
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = -1.1\text{A}$ (Note 2)		-0.7	-1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F = -1\text{A}, di/dt = 100\text{A}/\mu\text{s}$		21		ns
$Q_{rr}$	Reverse Recovery Charge			5		nC

#### Notes:

1:  $R_{\theta JA}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5\text{in.}$  board of FR-4 material. The thermal resistance from the junction to the circuit board side of the solder ball,  $R_{\theta JB}$  is defined for reference. For  $R_{\theta JC}$  the thermal reference point for the case is defined as the top surface of the copper chip carrier.  $R_{\theta JC}$  and  $R_{\theta JB}$  are guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.



a.  $83^\circ\text{C/W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper,  $1.5'' \times 1.5'' \times 0.062''$  thick PCB



b.  $140^\circ\text{C/W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width <  $300\mu\text{s}$ , Duty cycle < 2.0%.

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

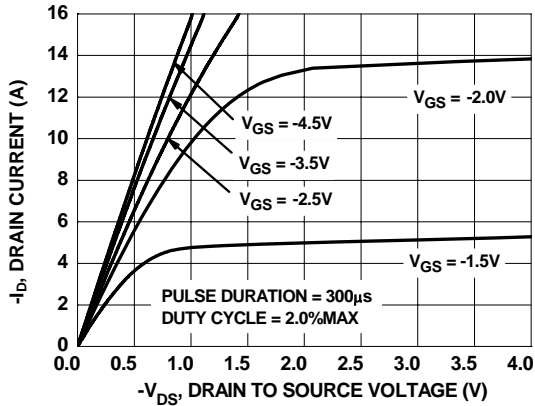


Figure 1. On Region Characteristics

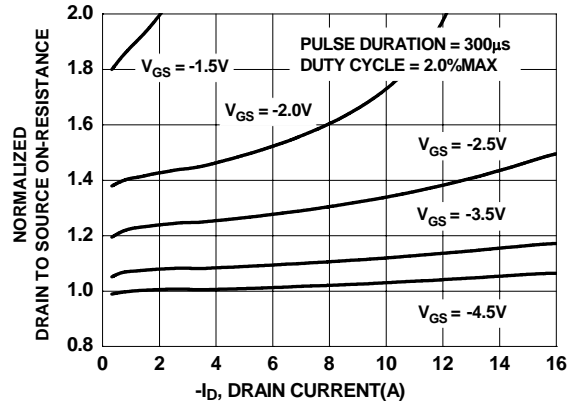


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

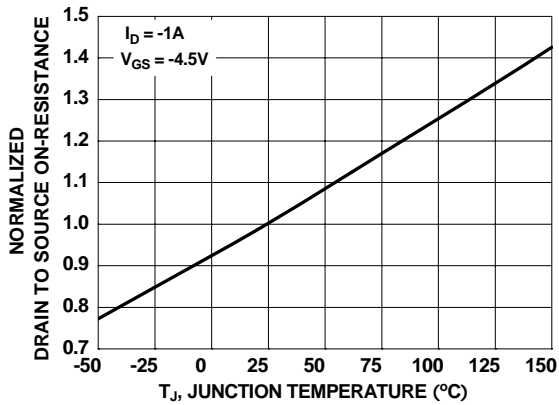


Figure 3. Normalized On Resistance vs Junction Temperature

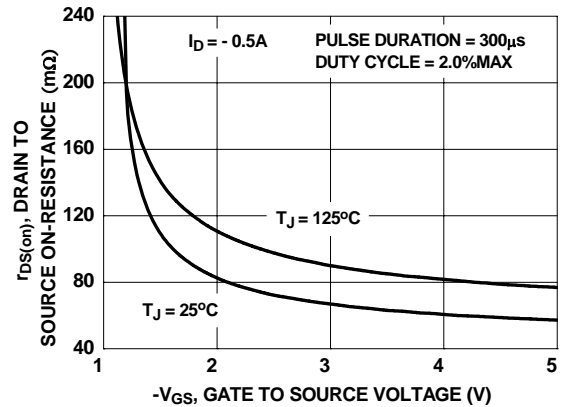


Figure 4. On-Resistance vs Gate to Source Voltage

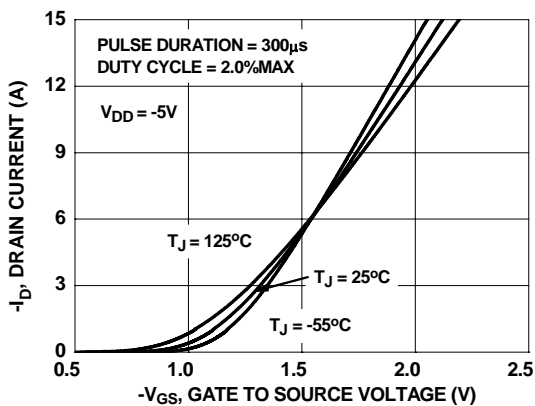


Figure 5. Transfer Characteristics

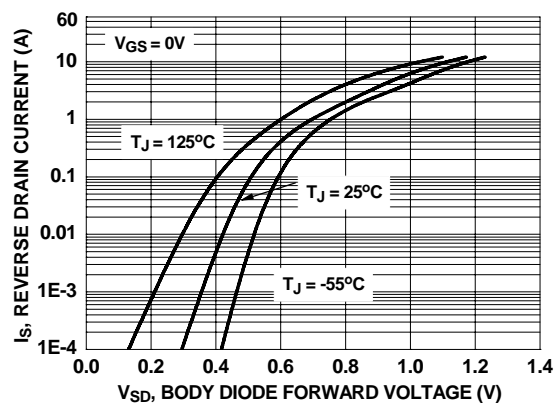
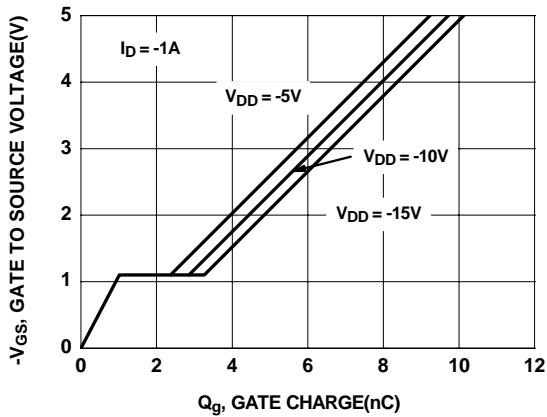
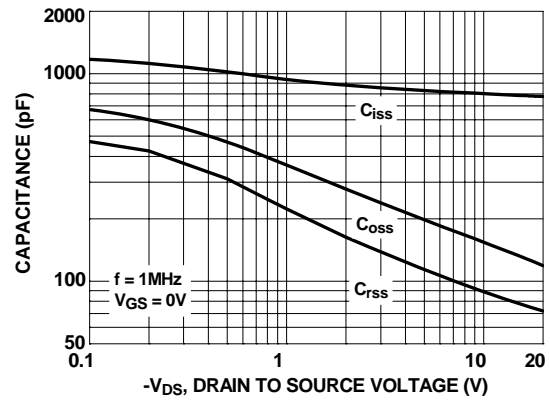


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

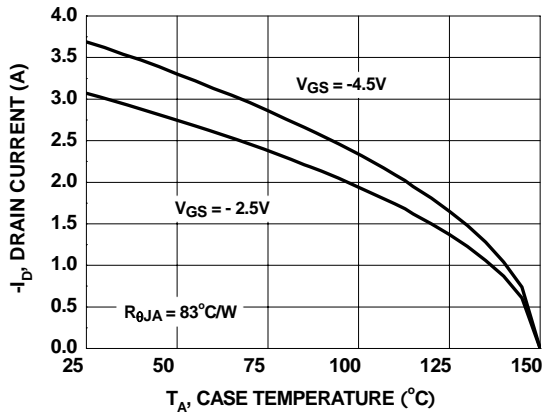
**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted



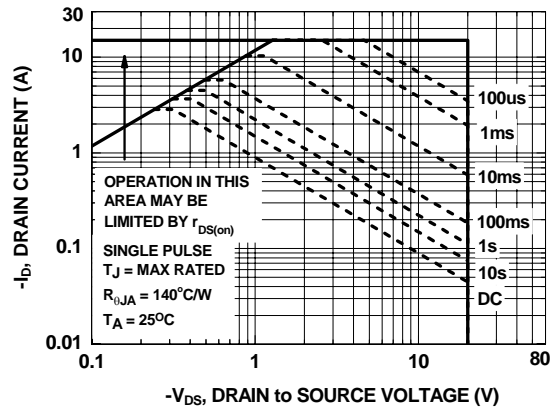
**Figure 7. Gate Charge Characteristics**



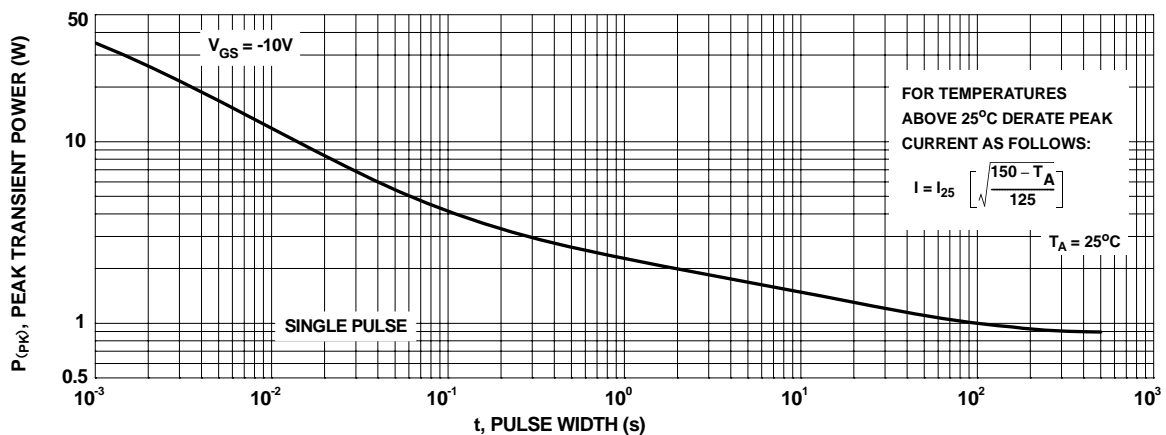
**Figure 8. Capacitance vs Drain to Source Voltage**



**Figure 9. Maximum Continuous Drain Current vs Ambient Temperature**

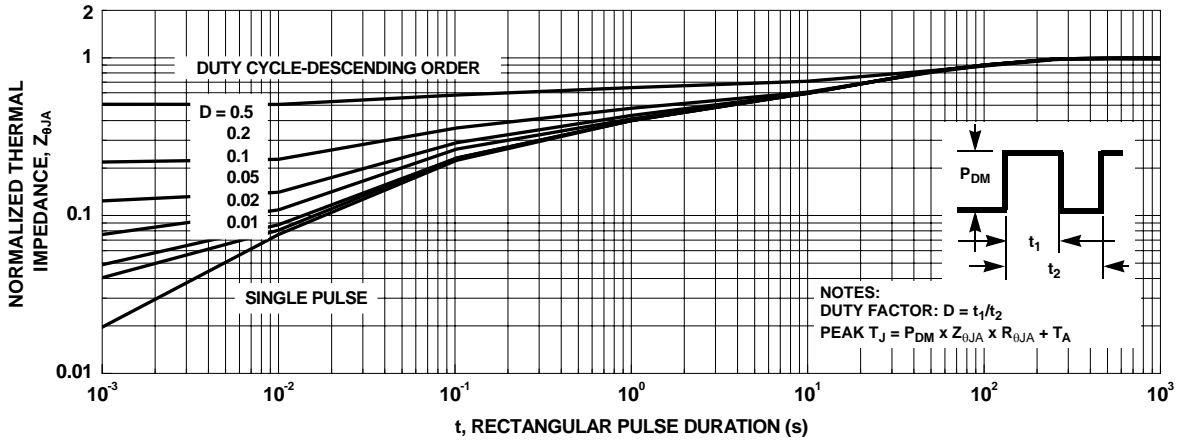


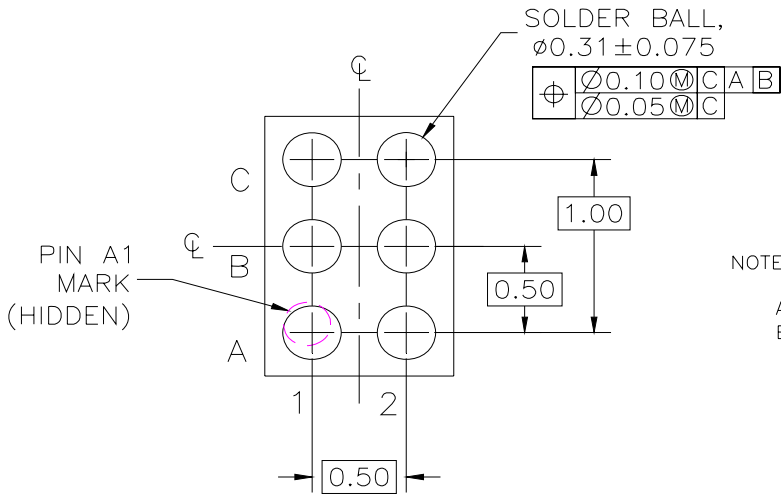
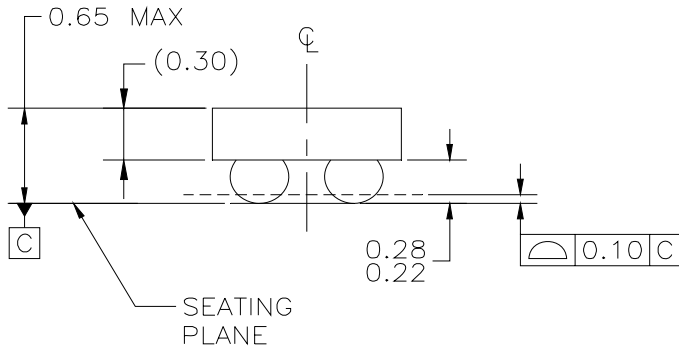
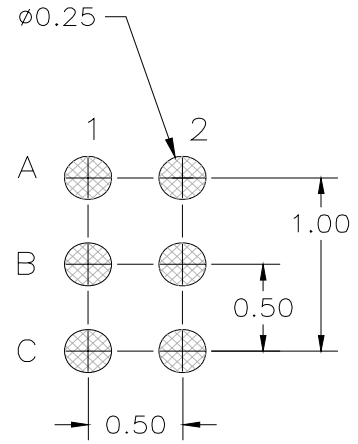
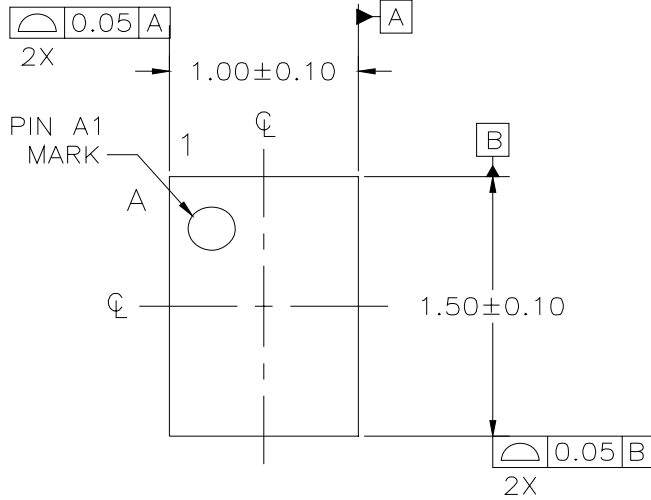
**Figure 10. Forward Bias Safe Operating Area**



**Figure 11. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted





NOTES: UNLESS OTHERWISE SPECIFIED

- A) ALL DIMENSIONS ARE IN MILLIMETERS.
- B) NO JEDEC REGISTRATION REFERENCE AS OF OCTOBER 2005.

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